

Product features

High precision machining technology

Low temperature drift, high power.

Ceramic substrate, 50 Ω coplanar waveguide

Gold wire bonding

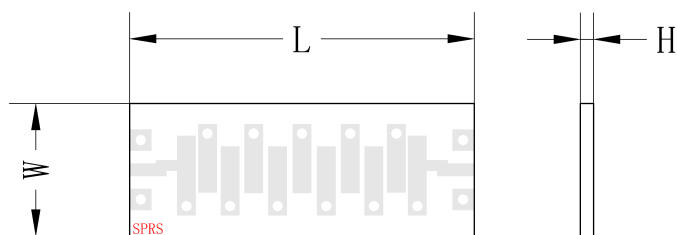
Tech specifications

Items	Parameters	Units
Center Frequency	3.95	GHz
Bandwidth	3.3-4.6	GHz
Center loss	2.2	dB
Ripple	1.0	dB
VSWR	1.7:1	
Group delay ripple	0.9	ns
Rejection	40@DC-2.6GHz	dBc
Rejection	40@5.4-9.8GHz	dBc

Other requirement (Design assurance)

power	2W CW
Operation Temp.	-55~+85°C
Storage Temp.	-55~+125°C
Outline size	L:8.0, W:6.0, h:0.39

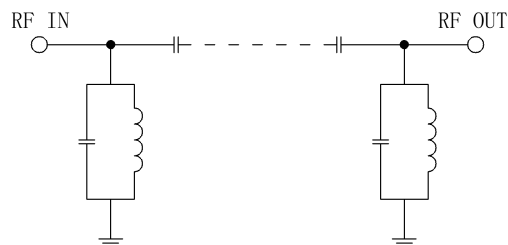
Outline drawing: Port centered



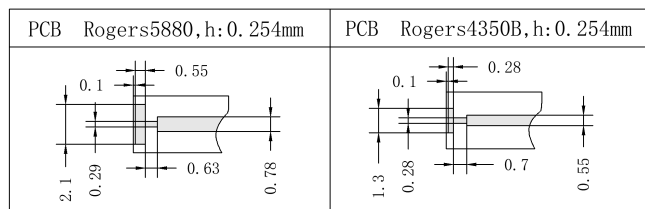
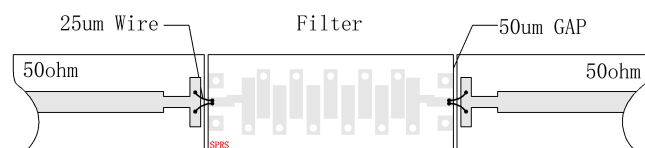
Reference picture



Schematic diagram



Suggested PCB Layout



Note

- 1: The chip is recommended to be used in separate chambers, with one side 0.1mm away from the side wall and the surface 2.61mm away from the top cover. The ports are interchangeable;
- 2: Suggest using conductive adhesive for bonding;
- 3: 芯片应安装在可伐(推荐) 或铜等与陶瓷热膨胀系数(6.7ppm /C)相近的材料, 载体厚度 $\geq 0.2\text{mm}$;
- 4: Suggest using a T-shaped structure for microstrip bonding.

Thin film filter STBP4R0-1R3-N048

Bandwidth 3.3-4.6GHz, Rejection 40@DC-2.6GHz, 40@5.4-9.8GHz

Typical test curve

